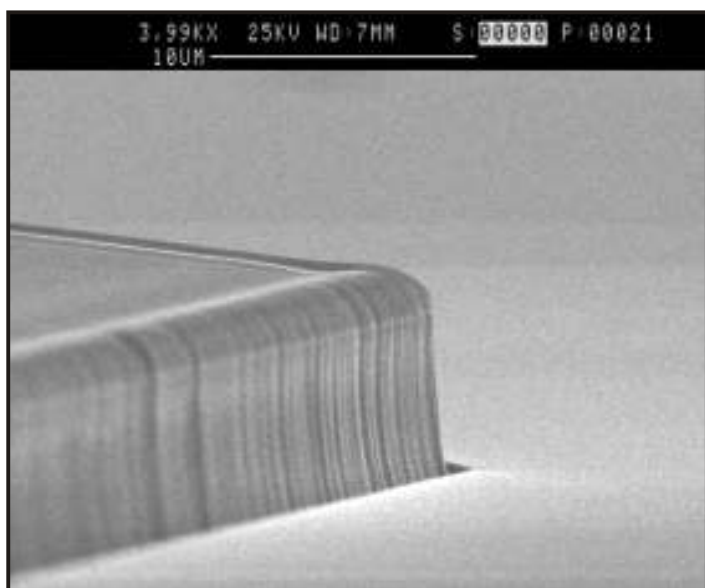
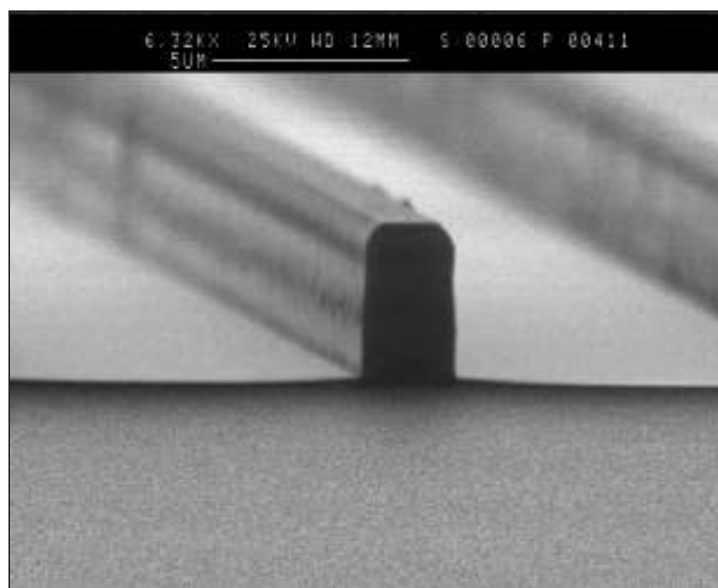


# Plasmalab Data

## III/ V Heterostructure RIE Etching



Pairs of InP/InGaAsP layers/ InP/ pairs of InGaAsP/InP with hard baked PR mask intact



DBR stack of (AlGa)InAs/(AlGa)InAs on InP with SiO<sub>2</sub> mask

### Plasmalab 80 Plus

### Plasmalab System 100/ 133

#### Technology:

- Parallel Plate Configuration
- RIE-Mode (13.56 MHz)
- Shower Head Gas Inlet
- Cl based process

#### Results:

- Rate : 60 - 90 nm/ min
- anisotropic profile
- good uniformity
- Mask: Photoresist (hard baked, UV cured) or SiO<sub>2</sub>

